

NCE N-Channel Enhancement Mode Power MOSFET

Description

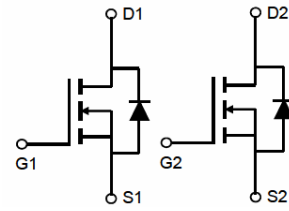
The NCE40ND0812S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

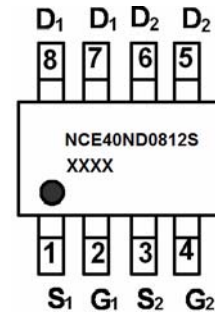
- $V_{DS} = 40V, I_D = 8A$ $V_{DS} = 40V, I_D = 12A$
 $R_{DS(ON)} < 18m\Omega @ V_{GS}=10V$ $R_{DS(ON)} < 14m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=4.5V$ $R_{DS(ON)} < 20m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current

Application

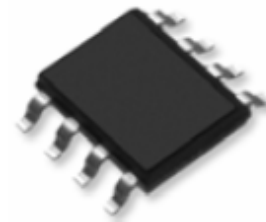
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40ND0812S	NCE40ND0812S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	N1-Channel	N2-Channel	Unit
Drain-Source Voltage		V_{DS}	40	40	V
Gate-Source Voltage		V_{GS}	± 20	± 20	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	8	12	A
	$T_C=100^\circ C$		5.7	8.5	
Pulsed Drain Current ^(Note 1)		I_{DM}	32	60	A
Maximum Power Dissipation	$T_C=25^\circ C$	P_D	2	2.5	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150		$^\circ C$

Thermal Characteristic

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient ^(Note 2) (N1-Channel)	$R_{\theta JA}$	62.5	85	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient ^(Note 2) (N2-Channel)	$R_{\theta JA}$	50	75	$^\circ C/W$

N1-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

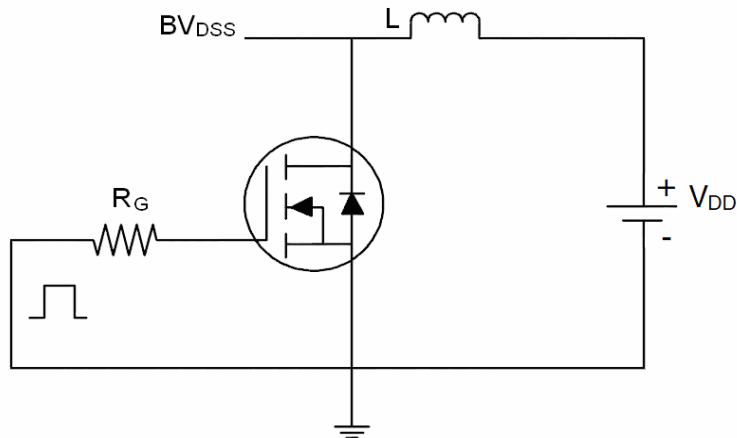
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A	-	15.8	18	mΩ
		V _{GS} =4.5V, I _D =4A	-	22	28	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =8A	33	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	964	-	PF
Output Capacitance	C _{oss}		-	109	-	PF
Reverse Transfer Capacitance	C _{rss}		-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =2.5Ω V _{GS} =10V, R _{GEN} =3Ω	-	5.5	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	22.9	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	nC
Gate-Drain Charge	Q _{gd}		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =8A	-	0.8	1.2	V

Notes:

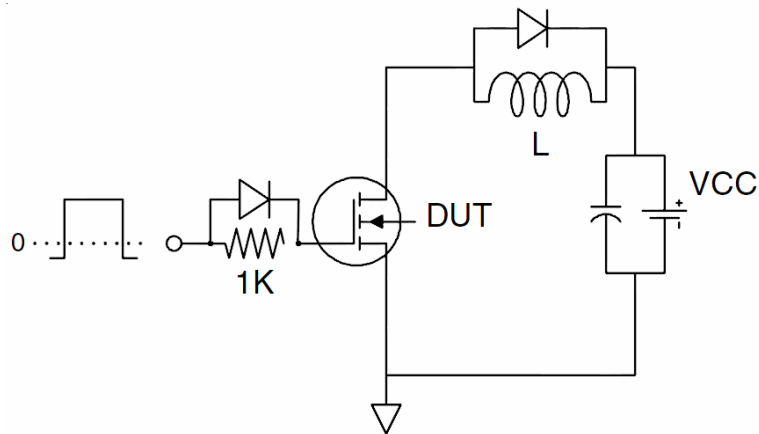
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. Surface Mounted on FR4 Board, t ≤ 10 sec. The current rating is based on the t ≤ 10s thermal resistance rating.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production.

Test Circuit

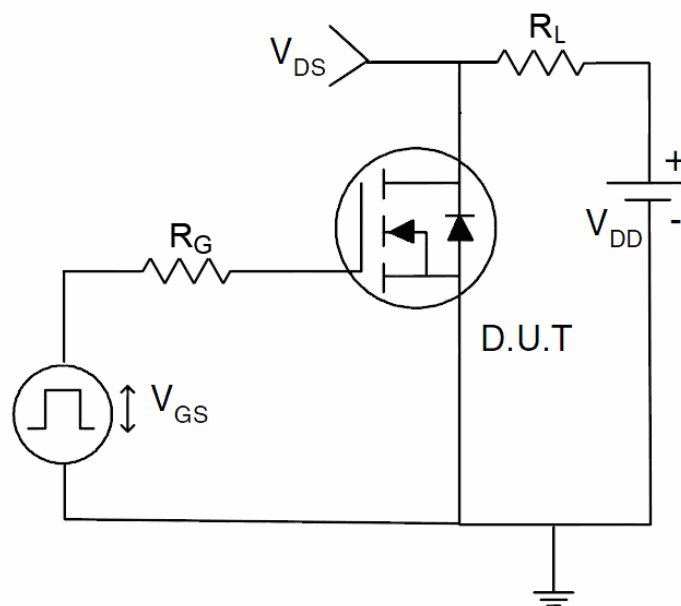
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



N1- Channel Typical Electrical and Thermal Characteristics (Curves)

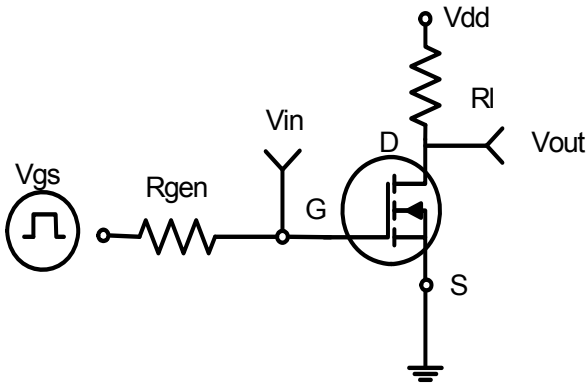


Figure 1: Switching Test Circuit

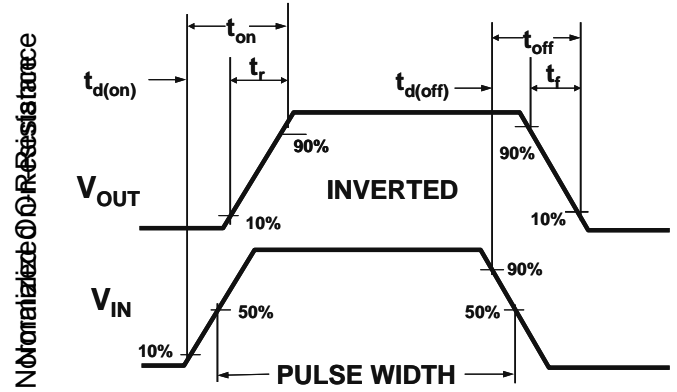


Figure 2: Switching Waveforms

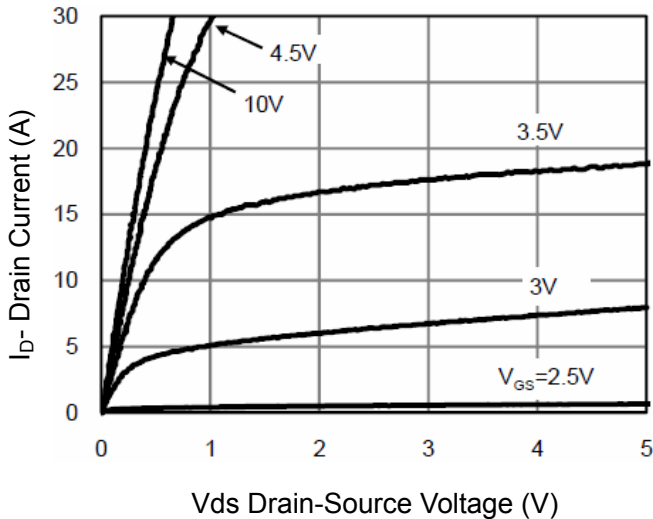


Figure 3 Output Characteristics

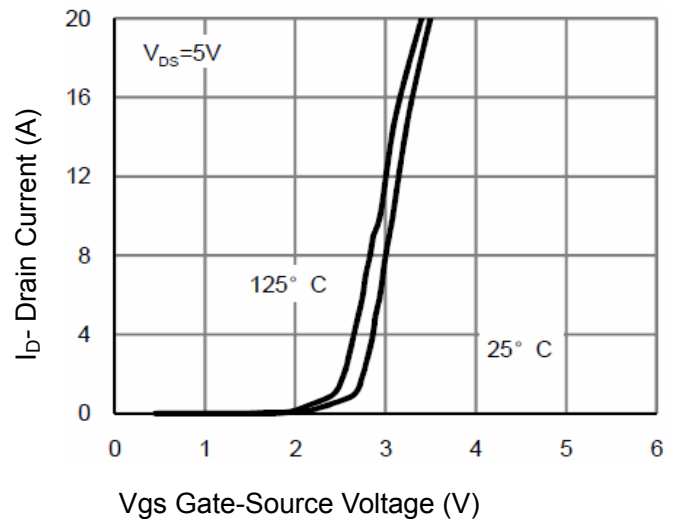


Figure 4 Transfer Characteristics

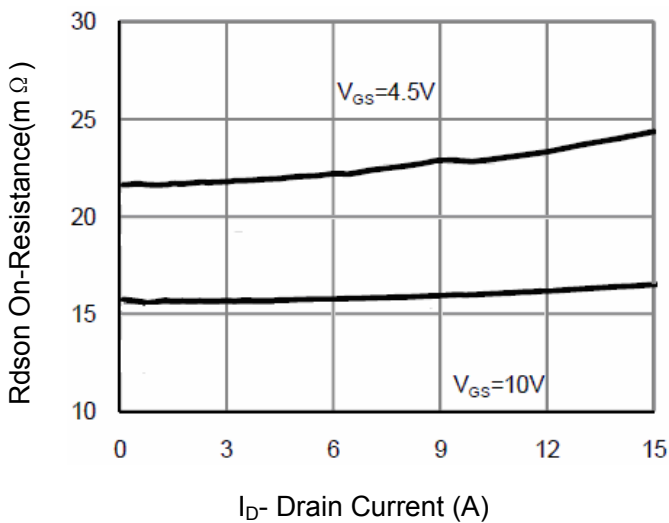


Figure 5 Drain-Source On-Resistance

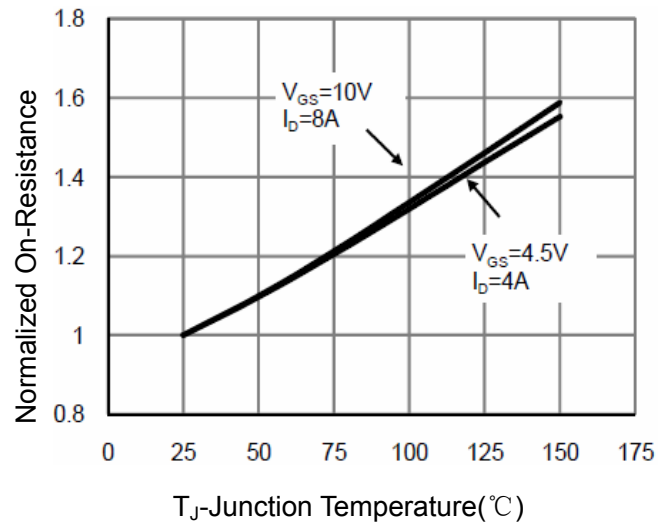
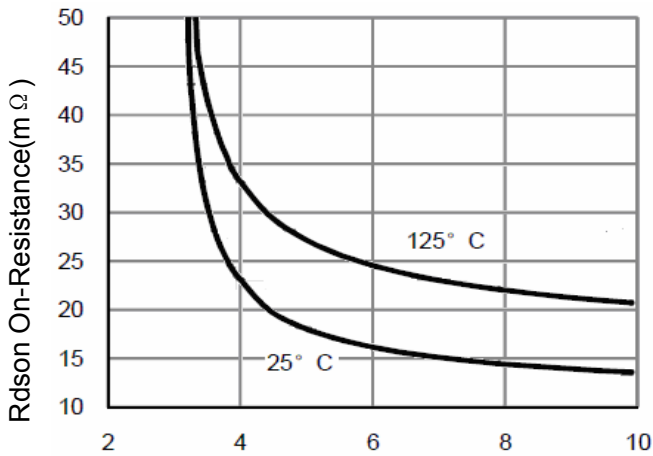
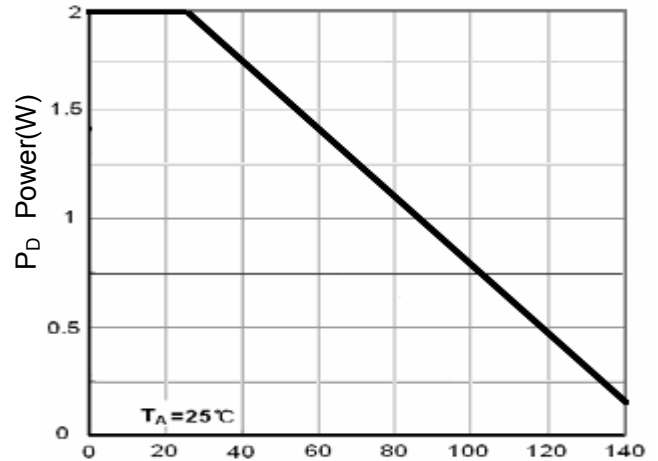


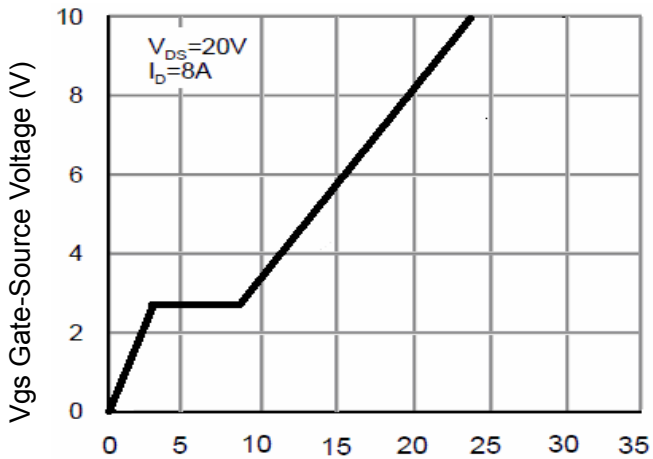
Figure 6 Drain-Source On-Resistance



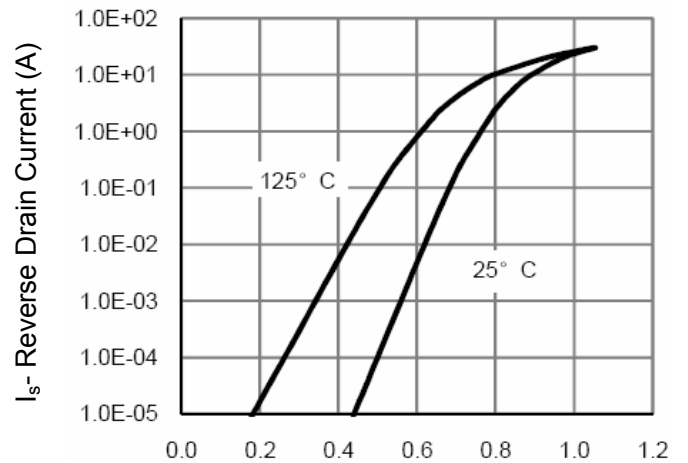
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



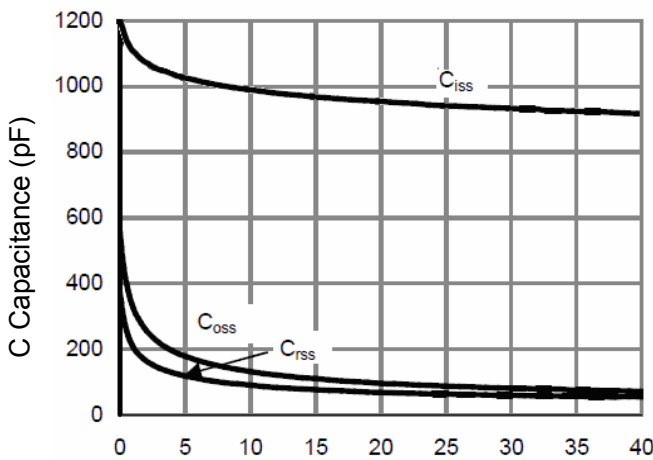
T_J-Junction Temperature(°C)
Figure 8 Power Dissipation



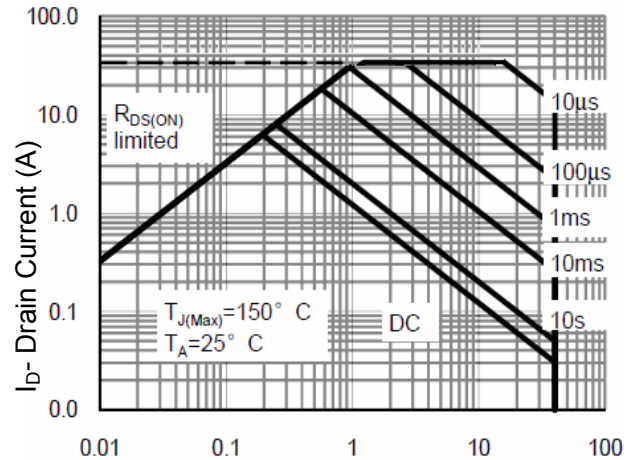
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

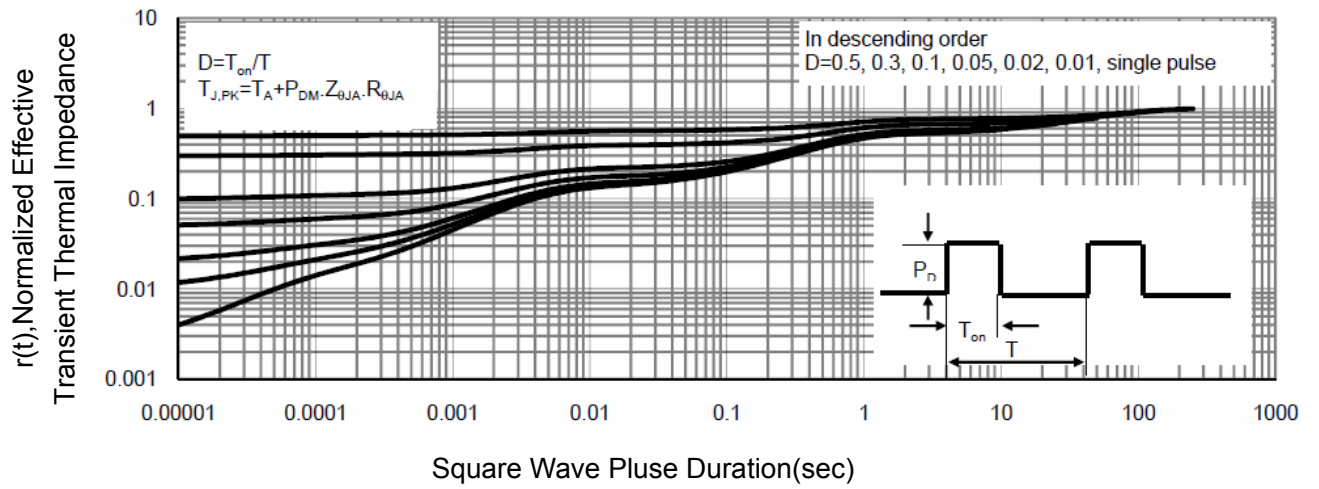


Figure 13 Normalized Maximum Transient Thermal Impedance

N2-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	11.7	14	mΩ
		V _{GS} =4.5V, I _D =8A	-	15.6	20	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10A		75	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	1780	-	PF
Output Capacitance	C _{oss}		-	209	-	PF
Reverse Transfer Capacitance	C _{rss}		-	160	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =2Ω V _{GS} =10V, R _G =3Ω	-	6.4	-	nS
Turn-on Rise Time	t _r		-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =10A, V _{GS} =10V	-	38.2		nC
Gate-Source Charge	Q _{gs}		-	5.6		nC
Gate-Drain Charge	Q _{gd}		-	7.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	12	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 10A di/dt = 100A/μs (Note3)	-	29	-	nS
Reverse Recovery Charge	Q _{rr}		-	26	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

N2-Typical Electrical and Thermal Characteristics (Curves)

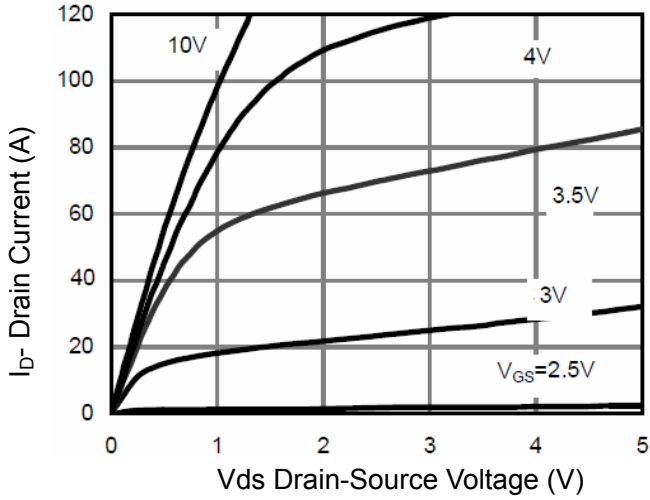


Figure 1 Output Characteristics

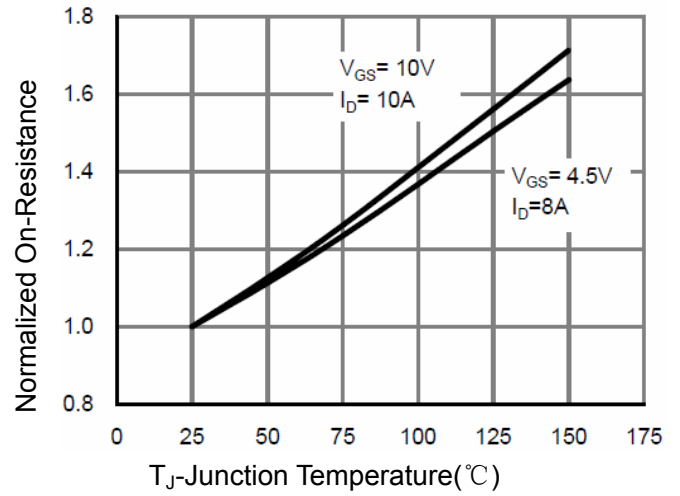


Figure 4 Rdson-Junction Temperature

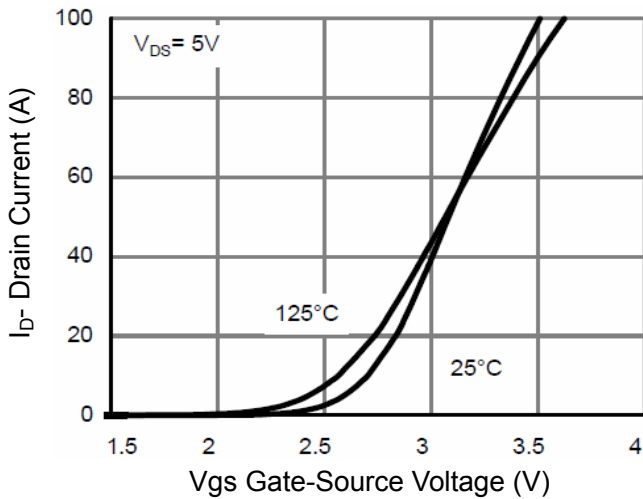


Figure 2 Transfer Characteristics

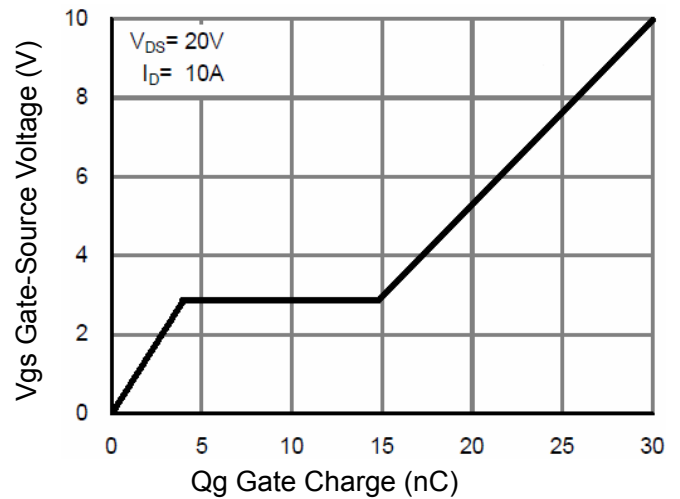


Figure 5 Gate Charge

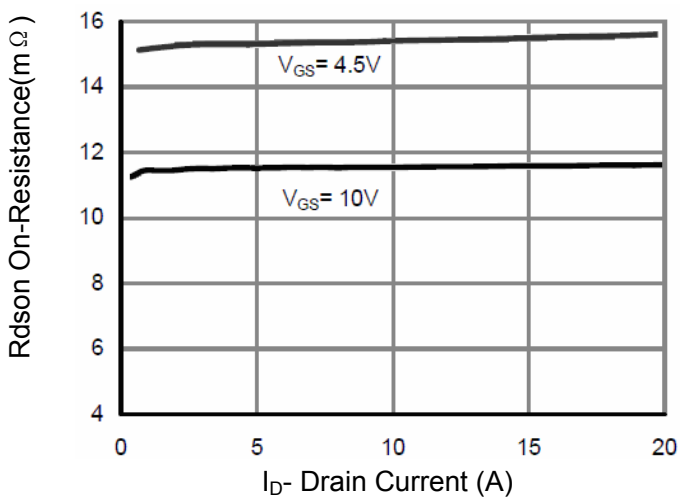


Figure 3 Rdson- Drain Current

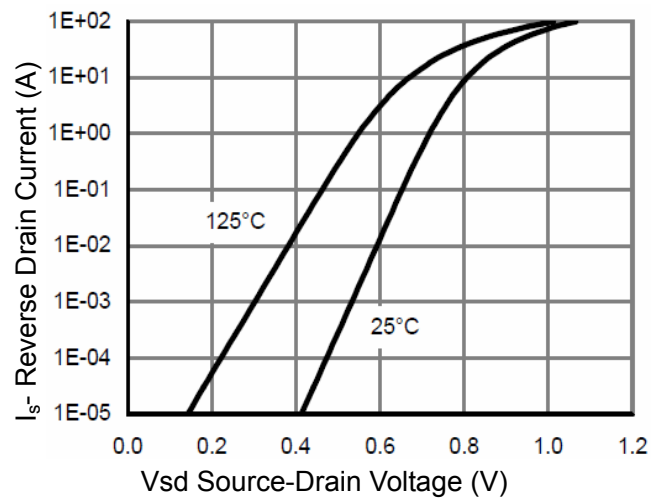


Figure 6 Source- Drain Diode Forward

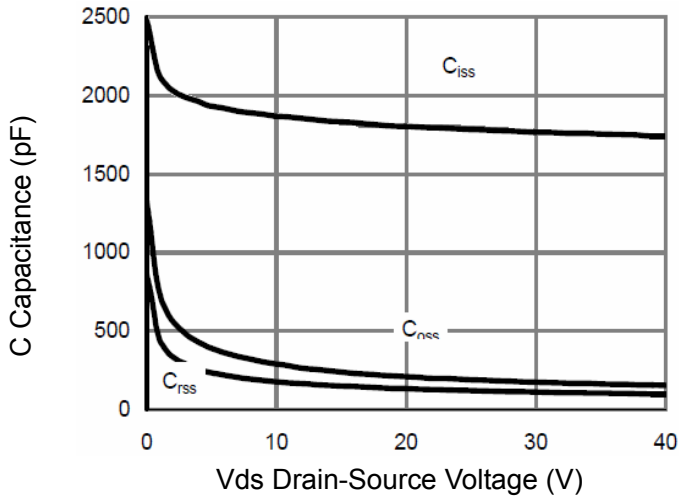


Figure 7 Capacitance vs Vds

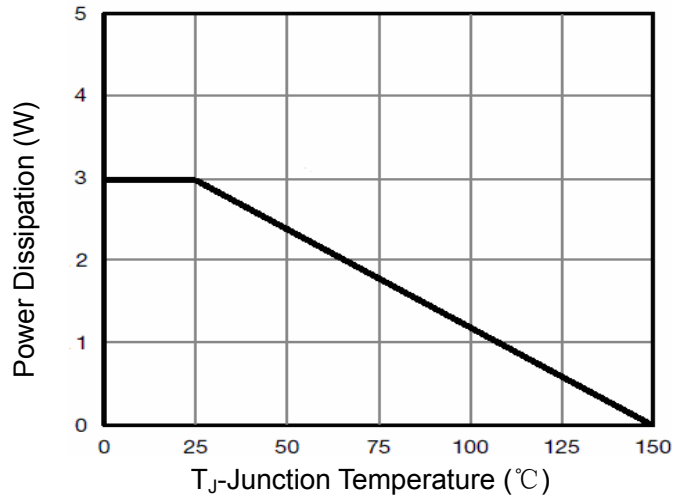


Figure 9 Power De-rating

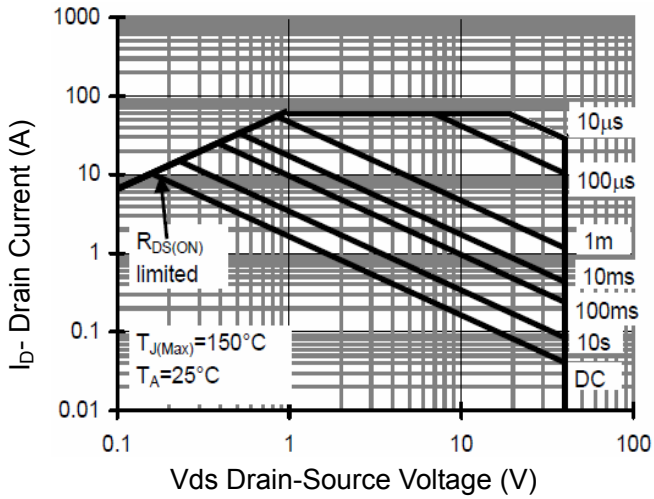


Figure 8 Safe Operation Area

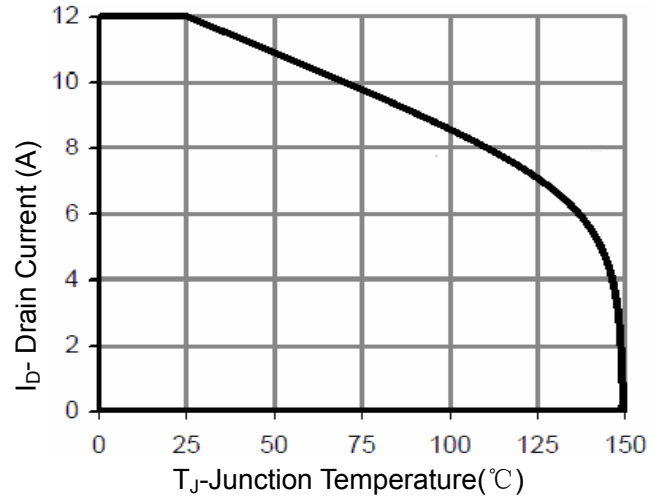


Figure 10 Current De-rating

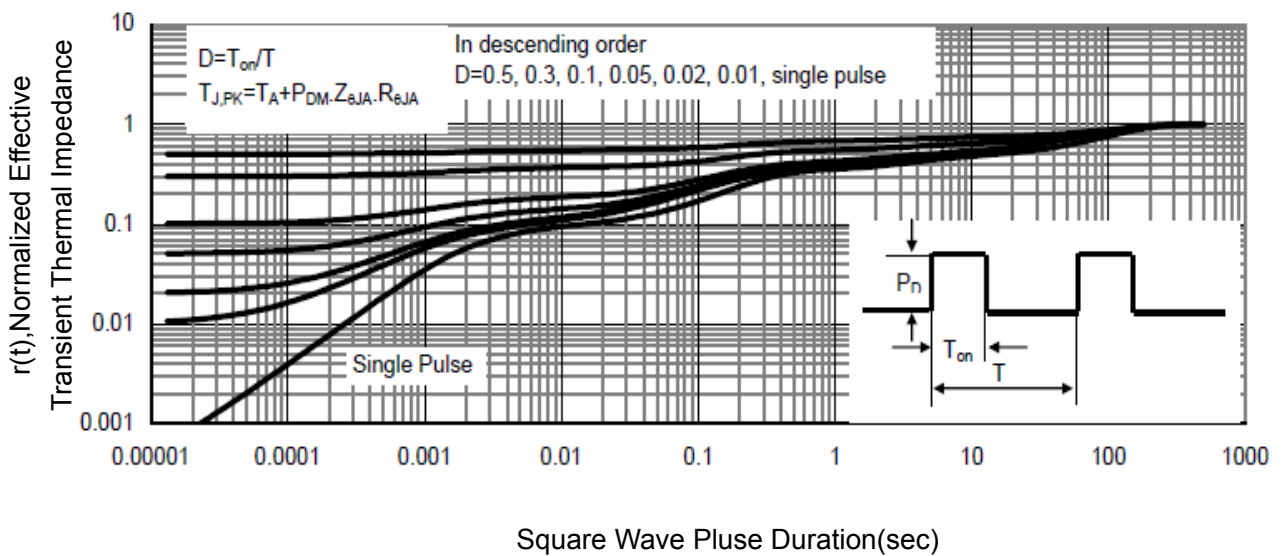
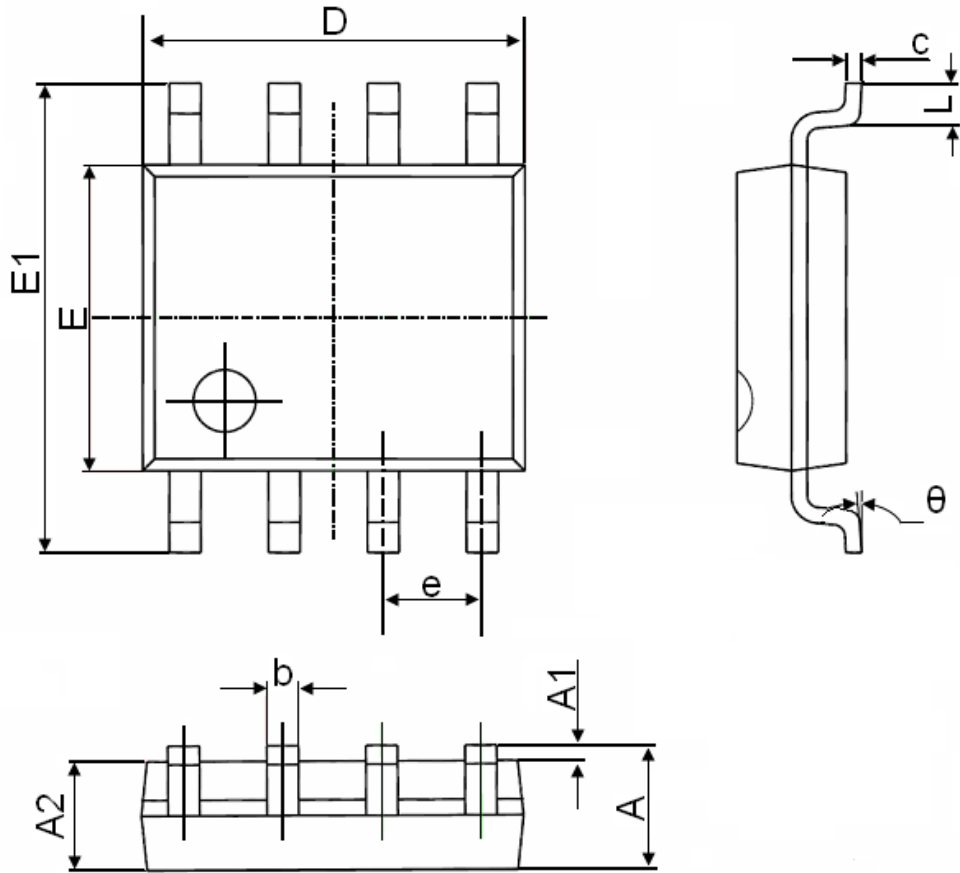


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°

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